



10/026,635, 014,274,412

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Masahiro FURUSAWA et al.

Application No.: 10/026,635

Filed: December 27, 2001

Docket No.: 111589

For: METHOD FOR MAKING THIN FILM AND ELECTRONIC APPARATUS

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office  
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 5, 7 and 8 as follows:

5. (Amended) A method for forming a thin film according to Claim 1, further comprising, before the step of placing the liquid, the step of forming an active region and an inactive region for the chemical vapor deposition in the surface for forming the thin film so that the thin film is selectively deposited.

7. (Amended) A method for forming a thin film according to Claim 1, wherein the step of vaporizing the raw material for the thin film is performed while supplying inert gas, hydrogen gas, or a mixture of inert gas and hydrogen gas parallel to the surface for placing the liquid of the substrate.

8. (Amended) A method for forming a thin film according to Claim 1, wherein the step of placing the liquid is performed by an ink-jet method.

REMARKS

Claims 1-9 are pending. By this Preliminary Amendment, claims 5, 7 and 8 are amended to remove multiple dependencies. Prompt and favorable examination on the merits is respectfully requested.

The attached Appendix includes marked-up copies of each rewritten claim (37 C.F.R. 1.121(c)(1)(ii)).

Respectfully submitted,



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Attachment:  
Appendix

Date: April 26, 2002

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DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461
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APPENDIX

Changes to Claims:

The following are marked-up versions of the amended claims:

~~-(5)-~~ 5. (Amended) A method for forming a thin film according to ~~any one of~~ Claims 1 ~~to~~ 4, further comprising, before the step of placing the liquid, the step of forming an active region and an inactive region for the chemical vapor deposition in the surface for forming the thin film so that the thin film is selectively deposited.

~~-(7)-~~ 7. (Amended) A method for forming a thin film according to ~~any one of~~ Claims 1 ~~to~~ 6, wherein the step of vaporizing the raw material for the thin film is performed while supplying inert gas, hydrogen gas, or a mixture of inert gas and hydrogen gas parallel to the surface for placing the liquid of the substrate.

~~-(8)-~~ 8. (Amended) A method for forming a thin film according to ~~any one of~~ Claims 1 ~~to~~ 7, wherein the step of placing the liquid is performed by an ink-jet method.